

DESCRIPTION:

This document describes Aplus 16G x 72-bit 16GB DDR3 SDRAM (Synchronous DRAM) Dual In-Line Memory Module. The components on this module include eighteen 1GB x 8-bit DDR3 SDRAMs in FBGA packages and a 2048-bit serial EEPROM. Those components were mounted on a 204-pin printed circuit board. This 204-pin SO-DIMM is used to be mounted into 204-pin edge connector sockets and data I/O transactions could be apply on both edges of DQS. The electrical and mechanical specifications are as follows:

FEATURES:

RoHS compliant products

JEDEC standard 1.5V \pm 0.075V power supply

1.5V \pm 0.075V power supply VDDQ

3.0V to 3.6V VDDSPD

Fast data transfer rates: PC3-12800

Nominal and dynamic on-die termination (ODT) for data strobe and mask signals

Single Rank

On-board IIC temperature sensor with integrated serial presence-detect (SPD) EEPROM

8 inter selectable burst chop BC4 and burst length BL8 on- the-fly (OTF)

Gold edge contacts

Terminated control, command, and address bus

DDR3 DRAM Speed

DDR3-1600 1600Mbps CL-tRCD-tRP 11-11-11

PERFORMANCE:

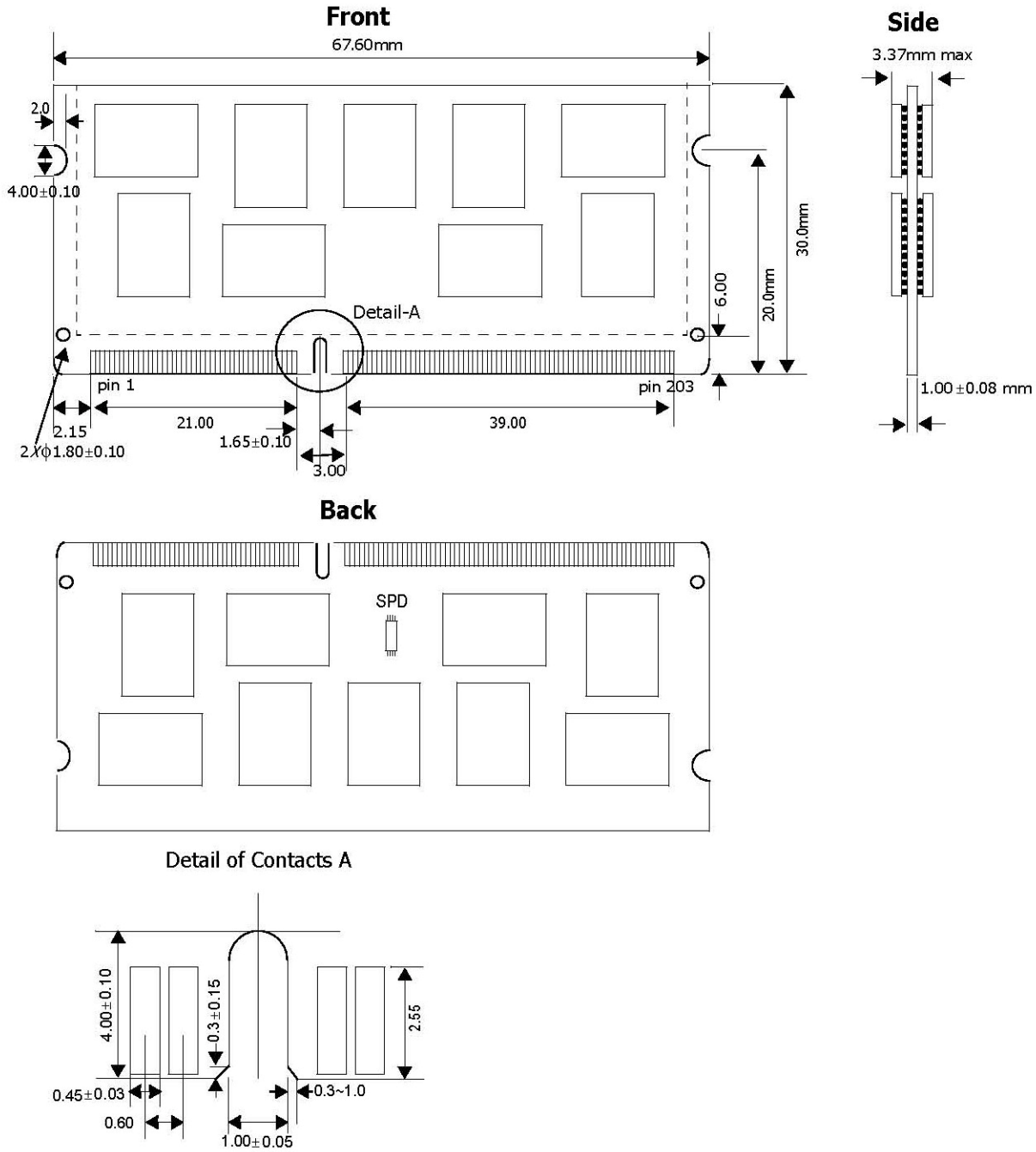
Clock Cycle Time (tCK) CL(1) 667

Clock Cycle Time (tCK) CL(1) 800

Row Cycle Time (tRC) 48.125ns for 1600

REFRESH Row Cycle Time (tRCD) 13.125ns

Memory Clock/Data Rate: 1.25ns/1600MT/s



Note:

1. ±0.13 tolerance on all dimensions unless otherwise stated.